VS-HFA16TB120SPbF

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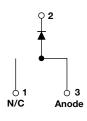
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COMPLIANT

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



www.vishay.com



PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK)
I _{F(AV)}	16 A
V _R	1200 V
V _F at I _F	2.3 V
t _{rr} (typ.)	30 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TB120SPbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120SPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED[®] product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120SPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	16						
Single pulse forward current	I _{FSM}		190	А					
Maximum repetitive forward current	I _{FRM}		64						
	Р	T _C = 25 °C	151	W					
Maximum power dissipation	PD	T _C = 100 °C	60	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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Document Number: 94594

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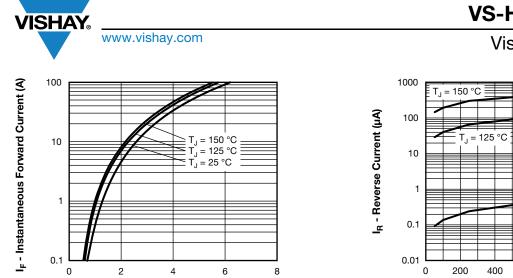
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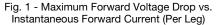
ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS						
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-			
		I _F = 16 A		-	2.5	3.0	V		
Maximum forward voltage	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93			
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7			
Maximum reverse		$V_{R} = V_{R}$ rated	Coofig 0	-	0.75	20			
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	375	2000	μΑ		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	27	40	pF		
Series inductance	L _S	Measured lead to lead 5 mm from p	backage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5 and 10	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 $	A/μs, V _R = 30 V	-	30	-			
	t _{rr1}	T _J = 25 °C		-	90	135	ns		
	t _{rr2}	T _J = 125 °C		-	164	245			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs	-	5.8	10	A		
	I _{RRM2}	T _J = 125 °C		-	8.3	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675			
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	680	1838	no		
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C]	-	120	-	A/µs		
See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	76	-	-7,μ5		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	К/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r.∕ w			
Maight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D ² PAK)		HFA16	TB120S				

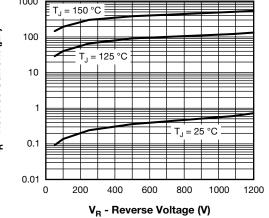


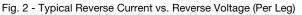
V_{FM} - Forward Voltage Drop (V)



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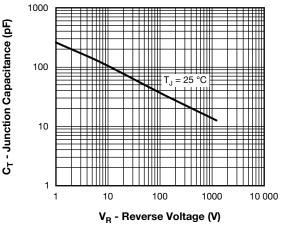


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

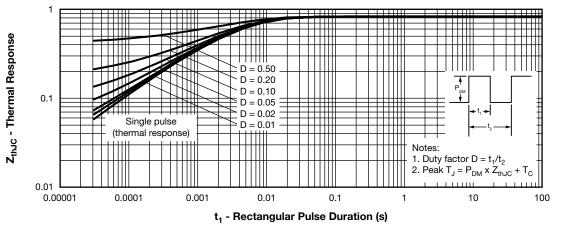
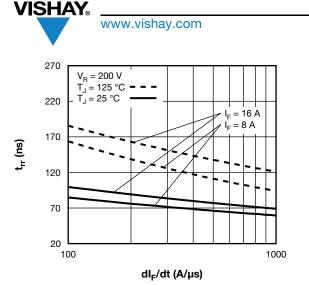
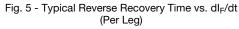


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

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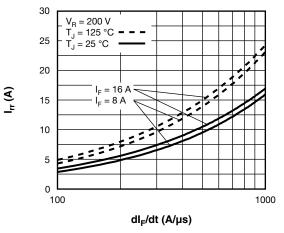


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

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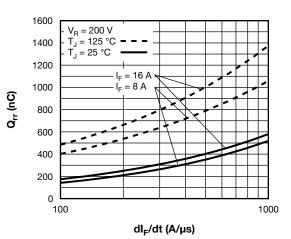


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

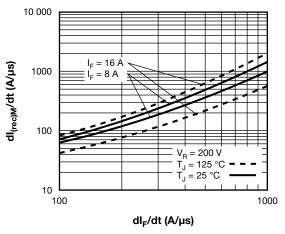


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

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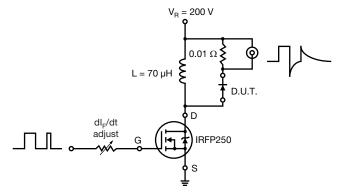
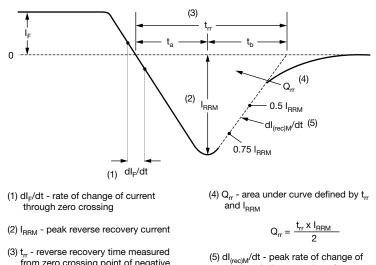


Fig. 9 - Reverse Recovery Parameter Test Circuit



from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	16	тв	120	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 - 4 - 5 -	HEX Pro Cur	KFRED [®] cess de rent rati	niconduo ⁹ family signator ng (16 = utline (TI	: A = ele : 16 A)	ectron ir		d	
	6 - 7 - 8 -	S =	age rati D ² PAK one = tu		= 1200	V)			
	9 -	• TF • Pt	RR = tap pF = lea	e and re be and re d (Pb)-fr Pb)-free	eel (righ ee, for	it orient tube pa	ed) ckaged		

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA16TB120SPBF	50	1000	Antistatic plastic tube							
VS-HFA16TB120STRRP	800	800	13" diameter reel							
VS-HFA16TB120STRLP	800	800	13" diameter reel							

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						



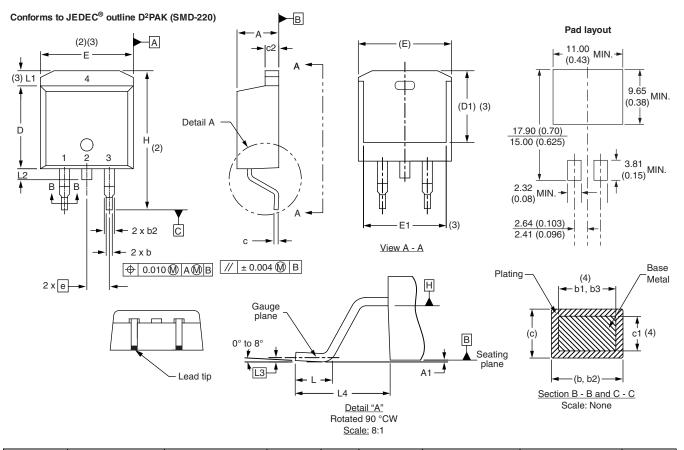
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Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES		SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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